



BZ5(2CZ117)

GLASS PASSIVATED SILICON RECTIFIER DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

| Parameter name | Symbols | Unit | Specifications | Test Condition |
|----------------------------------|-------------|------------------|---|--|
| Use for | | | Industrial frequency rectifier circuit. | |
| Store temperature | T | $^\circ\text{C}$ | -55~+150 | |
| Quality Class | | | JP, JT, JCT, GS, G, G+ | |
| Peak Repetitive Reverse Voltage | V_{RRM} | V | 50~1200 | |
| Average Forward Current | $I_{F(AV)}$ | A | 5.0 | |
| Peak Forward Voltage | V_{FM} | V | 2.2 | $I=I_{F(AV)}$ |
| Average Forward Voltage | V_F | V | 1.2 | $I=I_{F(AV)}$ |
| Non-repeat Forward Surge Current | I_{FSM} | A | 60 | Single-phase industrial frequency sine half wave 10ms |
| Peak Reverse Current | I_{RM1} | μA | 10 | $V_R=V_{RRM}, T_a=25^\circ\text{C}$ |
| Peak Reverse Current | I_{RM2} | μA | 200 | $V_R=V_{RRM}, T_a=125^\circ\text{C}$ |
| Junction Temperature | T_{jm} | $^\circ\text{C}$ | 150 | |

SPECIFICATIONS:

| A | B | C | D | E | F | G | H | I | J |
|-----|------|------|------|------|------|------|-------|-------|-------|
| 50V | 100V | 200V | 300V | 400V | 600V | 800V | 1000V | 1200V | 1400V |

Outline and Dimensions: